Program of Session B

Bulk Crystal Growth

B1: August 4 (Mond	ay), 14:00-15:15
Room: 313	
Chair: Liangbi Su	
14:00-14:30	B01 (Invited) Sapphire shaped crystal growth under stationary stable regime and the ways to overcome defects propagation Kheirreddine Lebbou, Institut Lumière Matière, Université de Lyon, FRANCE
14:30-14:45	B02 (Oral) Growth of rare earth orthochromites single crystals and properties study Roman Lanovsky, Institute of Solid State and Semiconductor Physics, Belarus National Academy of Sciences, BELARUS
14:45-15:00	B03 (Oral) Bubbles defects in sapphire single crystals grown by the Kyropoulos Technique under a reducing gas atmosphere Nicolas Pruneau, Institut Lumière Matière, FRANCE
15:00-15:15	B04 (Oral) Study on step growth of 3C-SiC based on lattice kinetic Monte Carlo method Wensen Ai, School of Energy and Power Engineering, Xi'an Jiaotong University, CHINA

B2: August 4 (Mo	onday), 16:00-17:15
Room: 313	
Chair: Kheirreddi	ine Lebbou
16:00-16:30	B05 (Invited)
	Achieving orientated crystal growth by self-seeding Bridgman method
	Hongsheng Shi, Zhejiang University of Science & Technology, CHINA
16:30-16:45	B06 (Oral)
	Challenges of energy consumption and crucible materials in bulk crystal growth from melt
	Kaspars Dadzis, Leibniz-Institut für Kristallzüchtung (IKZ), GERMANY
16:45-17:00	B07 (Oral)
	Single crystal growth and properties of complex oxyborates
	Sergei Barilo, Institute of Solid State and Semiconductor Physics, Belarus National
	Academy of Sciences, BELARUS

17:00-17:15 B08 (Oral)

Numerical study of heater length and crucible position in Continuous Czochralski Silicon Wenjia Su, Jiangsu University, CHINA

B3: August 5 (Tuesday), 11:00-12:15

Room: 313

Chair: Hongsheng Shi

Chair: Hongsneng S	DN1
11:00-11:30	B09 (Invited) Modified Bridgman growth and laser output properties of mid-infrared nonlinear optical crystal LiInX ₂ (X=S, Se) Shanpeng Wang, Shandong University, CHINA
11:30-11:45	B10 (Oral) In-situ monitoring of the interface flipping phenomenon during the growth of lithium niobate crystals Zhang Danyi, Sun Yat-sen University, CHINA
11:45-12:00	B11 (Oral) Temperature-dependent stability of SiC polytypes from DFT calculations Zahra Rajabzadeh, Montanuniversität Leoben, AUSTRIA
12:00-12:15	B12 (Oral) Growth and magneto-optical properties of rare earth iron garnet and perovskite single crystals Hui Shen, Shanghai Institute of Technology, CHINA

B4: August 5 (Tuesday), 14:00-15:30

Room: 313

Chair: Kozo Fujimara

14:00-14:30	B13 (Invited)
	Czochralski-growth and efficient laser operation of rare-earth-doped YScO3 crystals
	Christian Kränkel, Leibniz-Institut für Kristallzüchtung (IKZ), GERMANY
14:30-15:00	B14 (Invited)
	Crucible free bulk crystal growth of Ce:(Lu,Y) ₂ SiO ₅ scintillator
	Kei Kamada, Tohoku University, JAPAN
15:00-15:15	B15 (Oral)
	Experimental and numerical analysis of the heat transfer processes during the Czochralski
	growth of Li ₂ B ₄ O ₇ single crystals as a function of the solid-liquid interface gradient
	Jose Luis Plaza, Universidad Autonoma de Madrid, SPAIN
15:15-15:30	B16 (Oral)
	Crystal growth of LiTaO ₃ from the melt without precious metal crucibles

B5: August 5 (Tuesday), 16:00-17:15

Room: 313

Chair: Christian Kränkel

Taketoshi Tomida, C&A Corporation, JAPAN





The 21st International Conference on Crystal Growth and Epitaxy (ICCGE-21)

16:00-16:30	B17 (Invited)
	Growth of ultra-high temperature oxide crystals by Skull melting method
	Jiayue Xu, Shanghai Institute of Technology, CHINA
16:30-16:45	B18 (Oral)
	Magnetic spin textures in intercalated transition metal dichalcogenides
	Daniel Mayoh, University of Warwick, UNITED KINGDOM
16:45-17:00	B19 (Oral)
	Unlocking the hidden transition: Exploring non-polar to ferroelectric phase evolution in
	HfO ₂ -based bulk crystals
	Yihao Shen, Shandong University, CHINA
17:00-17:15	B20 (Oral)
	Computational analysis of radiation coefficient and axial position of the heat shield for
	Czochralski method β-Ga ₂ O ₃
	Wenjia Su, Jiangsu University, CHINA

B6: August 6 (Wednesday), 9:00-10:30	
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Room: 313 Chair: Jiayue Xu

09:00-09:30	B21 (Invited)
	Facet kinetics in silicon growth from the melt: experiments and hypotheses
	Thierry Duffar, Grenoble Institute of Technology, FRANCE
09:30-10:00	B22 (Invited)
	Rare earth doped alkaline earth fluoride mid-infrared laser crystals
	Zhen Zhang, Shanghai Institute of Ceramics, Chinese Academy of Sciences, CHINA
10:00-10:15	B23 (Oral)
	Numerical simulation of Sb-doped CZ-Si crystal growth for HV-IGBT
	Shin-ichi Nishizawa, Kyushu University, JAPAN
10:15-10:30	B24 (Oral)
	Influence of transverse magnetic field (TMF) coil geometry on oxygen transport during
	Czochralski silicon crystal growth
	Wenkai Liu, Shanghai Institute of Microsystem and Information Technology, Chinese
	Academy of Sciences, CHINA

B7: August 6 (Wednesday), 11:00-12:00

Room: 313

Chair: Thierry Duffar

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11:00-11:30	B25 (Invited)
	The engulfment of bubbles during bulk crystal growth
	Jeffrey J. Derby, University of Minnesota, UNITED STATES
11:30-11:45	B26 (Oral)
	Electric resistivity adjustment in Czochralski grown silicon crystals by combined control of
	doping species
	Xiaomin Han, Suzhou STR Software Technology Co.,Ltd., CHINA



11:45-12:00 B27 (Oral)

Batch growth of large LiB_3O_5 crystals with high quality at 4-kg level

Yinchao Yue, Henan Yueneng Photoelectric Technology Co., Ltd., Hebi, CHINA

B8: August 7 (Thursday), 11:00-12:00

Room: 313

Chair: Monica Cio	omaga Hatnean
11:00-11:30	B28 (Invited) Czochralski growth of large radiopure Li ₂ MoO ₄ single crystals for heat-scintillation cryogenic bolometers
	Matias Velazquez, Univ. Grenoble Alpes, CNRS, Grenoble INP, SIMAP, FRANCE
11:30-11:45	B29 (Oral)
	Investigations of the formation of the superconducting La ₃ Ni ₂ O ₇ single crystals under
	different growth conditions
	Daniel Mayoh, University of Warwick, UNITED KINGDOM
11:45-12:00	B30 (Oral)
	In-situ observation and numerical investigation of the solid-liquid interface in VB growth
	of fluoride crystals
	Yang Liu, Shanghai Institute of Ceramics, Chinese Academy of Sciences, CHINA

B9: August 7 (Thursday), 14:00-15:15

Room: 313

Chair: Jeffrey J. L	Perby
14:00-14:30	B31 (Invited) Crystal growth of rare earth silicates using a laser-diode-heated floating zone furnace Monica Ciomaga Hatnean, Paul Scherrer Institute, SWITZERLAND
14:30-14:45	B32 (Oral) Exploration of growth and doping in β-Ga ₂ O ₃ crystals via the micro-pulling down method Chaoyi Zhang, Tongji University, CHINA
14:45-15:00	B33 (Oral) Precursor engineering and liquid inclusions in solution-grown CsPbBr ₃ bulk crystal for radiation detection Ruichen Bai, Northwestern Polytechnical University, CHINA
15:00-15:15	B34 (Oral) Bulk crystals of Y:Zn _{1-x} Mg _x Te (x=0.05~0.18) (Y=Cr, Fe, P) were grown by travelling Te solution method Xiaoxiao Wei, Northwestern Polytechnical University, CHINA